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## **U.S. PATENT DOCUMENTS**

Examiner		Document No.	Name	Date	Class	Subclass	Filing Date
Initial '				·			(If appropriate)
a	AB	5,502,336	Park et al.	03/96			
Cn/	AC	5,479,054	Tottori	12/95		· · · · · · · · · · · · · · · · · · ·	
a	AD	5,338,700	Dennison et al.	08/94			
_or_	AE	4,974,040	Taguchi et al.	11/90			
On/	AF	5,150,278	Gonzallez et al.	09/92			
<u>Ca</u>	AG	5,196,910	Moriuchi et al.	03/93			
a	AH	5,605,857	Jost et al.	02/97			
a	ΑI	5,324,681	Lowrey et al.	06/94			
a	AJ_	5,292,677	Dennison	03/94			
on	AK	5,281,549	Fazan et al.	01/94	<u> </u>		
	AL						
	AM						

## FOREIGN PATENT DOCUMENTS

Document No.		Document No.	Date	Country	Translation
			·		(Yes or No)
<u>ol</u>	AN	61-176148	08/07/96	Japan	
_a_	AO	3-167874	07/19/91	Japan	
and	AP	5-218332	08/27/93	Japan	
	AQ				

29G

10-28-04

## **OTHER DOCUMENTS**

a	AR	B.LUTHER et al.; Planar Copper-Polyimide Back End of the Line"; Proceedings of 10 <sup>th</sup> International VMIC; pages 15-21; June 1993.	
<u>a</u>	AS	B.M. SOMERO et al.; "A Modular in-situ Integration Scheme for Deep Submicron", Proceedings of 10th International VMIC; pages 28-34; June 1993.	
_cn	AT	M.F. CHISHOLM et al.; "A High Performance 0.5 um Five-Level Metal Process with Extendibility of Sub-Half Micron"; pages 22-28; June 1994.	
_Cm.	AU	M. RUTTEN et al.; "Pattern Density Effects in Tungsten CMP", Proceedings of 12th International VMIC; pages 491-497; June 1995.	
on	AV	I. NAIKI et al.; "Center Wordline Cell: A New Symmetric Layout Cell for 64Mb SRAM"; Technical Digest of IEDM; pages 817-820; December 1993.	
<u>c</u>	A W	T. KAGA et al.; "A 0.29-um2 MIM-Crown Cell and Process Technologies for 1-Gigabit DRAMs"; Technical Digest of IEDM; pages 927-929; December 1994.	
<u>cn</u>	AX	H.K. KANG et al.; "Highly Manufacturable Process Technology for Reliable 256 Mbit and 1 Gbit DRAMs"; Technical Digest of IEDM; pages 635-638; December 1994.	
-Co-	A Y	Y. OHJI et al.; "Ta <sub>2</sub> O <sub>5</sub> Capacitors Dielectric Material for Giga-bit DRAMs"; Technical Digest of IEDM; pages 111-114; December 1995.	
<u></u>	AZ	Y. NISHIOKA et al.; "Giga-bit Scale DRAM Cell with New Simple Ru/(Ba,Sr)TiO3/Ru Stacked Capacitors Using X-ray Lithography"; Technical Digest of IEDM; pages 903-906; December 1995.	
<u>_</u> cw_	ВА	K.P. LEE et al.; "A Preocess Technology for 1 Giga-bit DRAM"; Technical Digest of IEDM; pages 907-910; December 1995.	
_cn	ВВ	J.K. PARK et al.; "Isolation Merged Bit Line Cell(IMBC) for 1Gb DRAM and Beyond". Technical Digest of IEDM; pages911-914; December 1995.	
	вс		
	BD		
Examiner	<i>C</i>	29G Date Considered 10-28-04	
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